

Silicon NPN Power Transistors

2N6492

DESCRIPTION

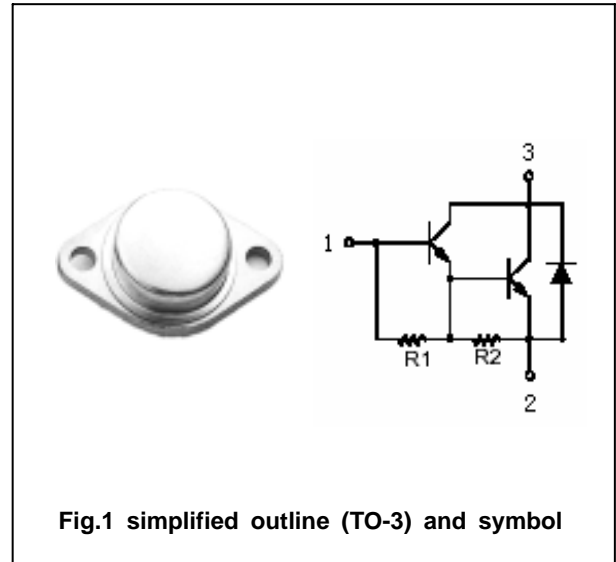
- With TO-3 package
- Low collector saturation voltage
- High DC current gain
- DARLINGTON

APPLICATIONS

- General-purpose power amplifier and low frequency swithing applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a =$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	55	V
V_{CEO}	Collector-emitter voltage	Open base	45	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		15	A
P_D	Total Power Dissipation	$T_C=25$	100	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-65~200	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-c}$	Thermal resistance junction to case	1.75	/W

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CHARACTERISTICS

T_m=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =0.1 A ; I _B =0	45			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =10A ; I _B =100mA			3.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =10A ; I _B =100mA			4.0	V
V _{BE}	Base-emitter on voltage	I _C =3A ; V _{CE} =4V			2.8	V
I _{CEO}	Collector cut-off current	V _{CE} =40V ; I _B =0			1.0	mA
I _{CEx}	Collector cut-off current	V _{CE} =55V ; V _{BE(off)} =-1.5V			0.5	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V ; I _C =0			3.0	mA
h _{FE-1}	DC current gain	I _C =3A ; V _{CE} =4V	500			
h _{FE-2}	DC current gain	I _C =15A ; V _{CE} =4V	100			

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PACKAGE OUTLINE

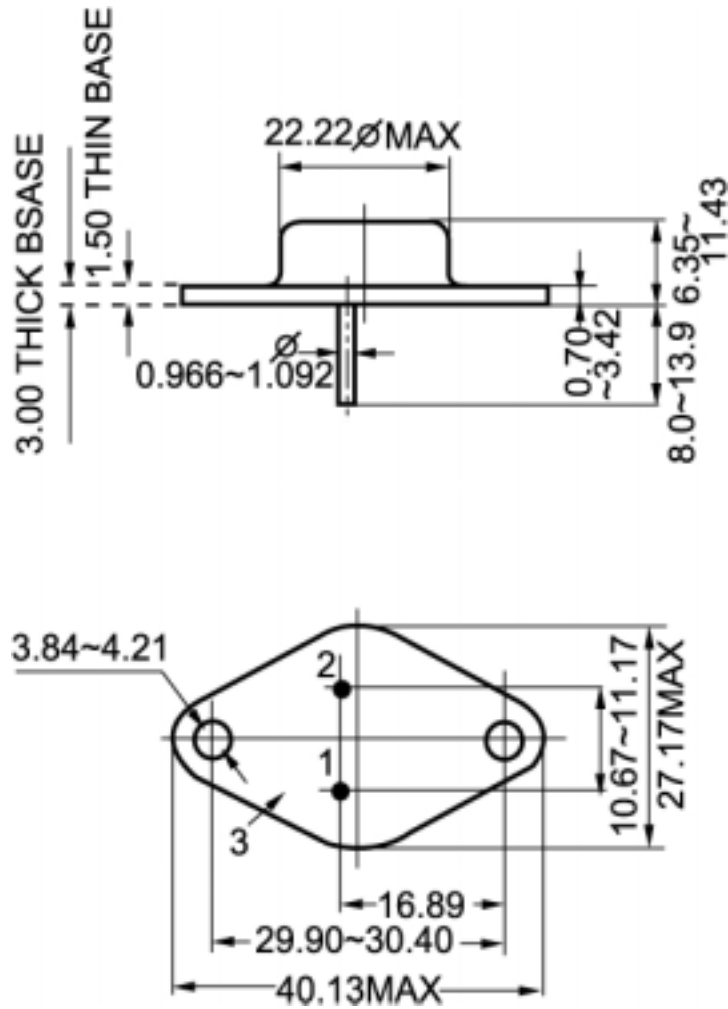


Fig.2 outline dimensions (unindicated tolerance: ± 0.10 mm)